

23. The method of Claim 22 further comprising growing said quantum well layer with a wurtzite crystal structure with said selected facet orientation tilted from the {0001} direction of said wurtzite crystal structure at an angle selected from about 80° to about 100°.

IN THE ABSTRACT

Please amend the abstract as follows. Attachment A provides a marked up version of the abstract containing the newly introduced changes.

A1  
A method for fabricating a light-emitting semiconductor device including a III-Nitride quantum well layer includes selecting a facet orientation of the quantum well layer to control a field strength of a piezoelectric field and/or a field strength of a spontaneous electric field in the quantum well layer, and growing the quantum well layer with the selected facet orientation. The facet orientation may be selected to reduce the magnitude of a piezoelectric field and/or the magnitude of a spontaneous electric field, for example. The facet orientation may also be selected to control or reduce the magnitude of the combined piezoelectric and spontaneous electric field strength.